

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3	(common adj substrate) with (low adj (doping or concentration or impurity)) with resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 06:00
L2	3	(common adj substrate) same (low adj (doping or concentration or impurity)) same resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 06:01
L3	247	(common adj substrate) and (low adj (doping or concentration or impurity)) and resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 06:18
L4	7	(silicon adj wafer) with (low adj (doping or concentration or impurity)) with resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 06:21
L5	22	(silicon adj wafer) same (low adj (doping or concentration or impurity)) same resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 06:23
L6	1664	(silicon adj wafer) and (low adj (doping or concentration or impurity)) and resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 06:28
L7	0	(injected adj current) with (common adj substrate) with ground	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 06:29
L8	0	(injecting adj current) with (common adj substrate) with ground	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 06:29
L9	0	(injection adj current) with (common adj substrate) with ground	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 06:29
L10	0	(inject\$ adj current) with (common adj substrate) with gnd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 06:31

L11	0	(buried adj region) with (lower adj resistance) with (common adj substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 06:46
L13	0	(buried adj region) same (lower adj resistance) same (common adj substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 06:47
L14	12	(buried adj region) and (lower adj resistance) and (common adj substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 06:47
L15	3	(embedded adj region) with (lower adj resistance) with (common adj substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 06:46
L16	0	(imbedded adj region) same (lower adj resistance) same (common adj substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 06:47
L17	3	(embedded adj region) same (lower adj resistance) same (common adj substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 06:47
L18	3	(embedded adj region) and (lower adj resistance) and (common adj substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 06:56
L19	451	257/499.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 06:58
L20	359	257/798.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 06:59
L21	70	257/920.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 07:04

L22	324	257/133.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 08:10
L23	799	noise adj isolation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 07:52
L24	250	(noise adj isolation) and (ic or (integrated adj circuit))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 08:46
L25	0	bartlett-donald.inv.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 07:55
L26	37	bartlett-donald\$.inv.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 07:55
L27	504	257/256.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 08:11
L29	226	257/263.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 08:12
L30	53	257/265.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 08:11
L31	280	257/272.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 08:12
L33	46	(circuit adj isolation) with noise	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 08:46